CMOS Digital Integrated Circuits Silicon Monolithic

# TDS4A212MX,TDS4B212MX

### 1. Functional Description

1-32Gbps 1-Lane Two Differential Channel, 2:1 Mux/1:2 De-Mux

### 2. General

TDS4A212MX, TDS4B212MX are high-speed differential channel multiplexer(Mux)/demultiplexer(De-Mux) switches. These devices are designed to support up to 32Gbps high-speed differential interfaces such as PCIe® 5.0, CXL 2.0, USB4<sup>®</sup> Version 2.0, Thunderbolt<sup>TM</sup> 4, DisplayPort<sup>TM</sup> 2.0.

TDS4A212MX and TDS4B212MX have different pin assignment. TDS4B212MX has an optimized pin assignment to achieve high frequency performance, while TDS4A212MX's pin assignment is easy to use for board layout.

The A Port (An+, An-) is connected to either the B Port (Bn+, Bn-) or C Port (Cn+, Cn-), which is determined by the combination of both the select (SEL) and output enable (OE). When the output enable (OE) is held at a highlevel, the switches are open (high-impedance state), regardless of the state of the select, thus these devices have lower consumption current.

The devices are designed to operate in temperatures from -40 °C to 105 °C and can be used for application including industrial use cases.

### 3. Features

- (1)Operating voltage:  $V_{CC} = 1.6$  to 3.6 V
- Operating temperature :  $T_{\rm opr}$  = -40 to 105  $^{\circ}\text{C}$ (2)
- Low current consumption For active mode (Typ.)  $: I_{ope} = 60 \ \mu A$ , (3)

For standby mode (Max) : $I_{STB}$ = 10 $\mu$ A
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(4)	-3-dB Bandwidth (differential) BW <sub>(Diff)</sub> (Typ.) :	TDS4B212MX = 27.5 GHz
		TDS4A212MX = 26.2 GHz
(5)	Differential insertion Loss DDIL (Typ.) :	TDS4B212MX = -1.4  dB @ f = 16  GHz
		TDS4A212MX = -1.9  dB @ f = 16  GHz
(6)	Differential return Loss DDRL (Typ.) :	TDS4B212MX = -16  dB @ f = 16  GHz
		TDS4A212MX = -18  dB @ f = 16  GHz
(7)	Differential Off Isolation DDOIRR (Typ.) :	TDS4B212MX = -14  dB @ f = 16  GHz
		TDS4A212MX = -11  dB @ f = 16  GHz
(8)	Differential Crosstalk DDXT (Typ.) :	TDS4B212MX = -36  dB @ f = 16  GHz
		TDS4A212MX = -30  dB @ f = 16  GHz

#### (9)Package: XQFN16

### 4. Interfaces

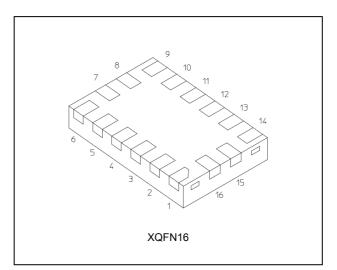
· PCIe 5.0/4.0	$\cdot$ Thunderbolt 4/3
· CXL 2.0/1.0	· DisplayPort 2.0/1.4
$\cdot$ USB4 Version 2.0, Gen3/Gen2	$\cdot$ USB 3.2 Gen 2/Gen 1
$\cdot$ SAS 3.0	

· PCIe<sup>®</sup> is a registered trademark of PCI-SIG.

- · USB4® is a registered trademark of USB Implementers Forum.
- · Thunderbolt<sup>TM</sup> is a trademark of Intel Corporation or its subsidiaries.
- · DisplayPort<sup>™</sup> is a trademark owned by the Video Electronics Standards Association (VESA®) in the United States and other countries.
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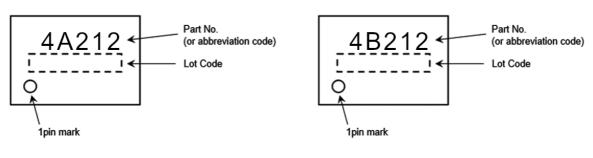
Start of commercial production 2024-05

### 5. Packaging



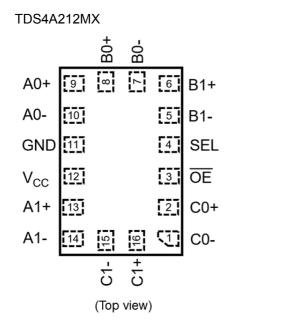
### 6. Marking

TDS4A212MX



TDS4B212MX

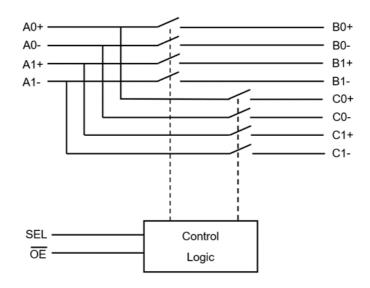
### 7. Pin Assignment



TDS4B212MX B0+ ВQ ~ ø 6 A0-9 C0-A0+ 10 5 C0+ GND 11  $V_{CC}$ 4 SEL 12 3 ŌĒ A1+ 13 2 B1+ ত্র 15 16 A1-14 B1-C1+ ά

(Top view)

### 8. Block Diagram



### 9. Principle of Operation

### 9.1. Truth Table

Inputs OE	Inputs SEL	Function					
L	L	An+ port = Bn+ port, An- port = Bn- port	(n=0,1)				
L	Н	An+ port = Cn+ port, An- port = Cn- port	(n=0,1)				
Н	_	An, Bn, Cn port Disconnect	(n=0,1)				

—: Don't care

### 10. Absolute Maximum Ratings (Note)

Characteristics	Symbol	Rating	Unit
Supply voltage	V <sub>CC</sub>	-0.5 to 4.0	V
Input voltage (OE, SEL)	V <sub>IN</sub>	-0.5 to 4.0	V
Switch I/O voltage	Vs	-0.5 to 2.5	V
Switch I/O current	۱ <sub>S</sub>	32	mA
Power dissipation	P <sub>D</sub>	180	mW
V <sub>CC</sub> /ground current	I <sub>CC</sub> /I <sub>GND</sub>	±50	mA
Storage temperature	T <sub>stg</sub>	-65 to 150	°C

Note: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

### 11. Operating Ranges (Note)

Characteristics	Symbol	Rating	Unit
Supply voltage	V <sub>CC</sub>	1.6 to 3.6	V
Input voltage (OE, SEL)	V <sub>IN</sub>	0 to 3.6	V
Signal pins differential voltage.	V <sub>I/O(Diff)</sub>	0 to 1.8	V
Signal pins common mode voltage.	V <sub>I/O(Com)</sub>	0 to 2.0	V
Operating temperature	T <sub>opr</sub>	-40 to 105	°C
Input rise and fall times	dt/dv	0 to 10	ns/V

Note: The operating ranges must be maintained to ensure the normal operation of the device. Unused control inputs must be tied to either  $V_{CC}$  or GND.

### 12. Electrical Characteristics

### 12.1. DC Characteristics

### 12.1.1. DC Characteristics (Note) (Unless otherwise specified, $T_a = -40$ to 85 °C)

Characteristics	Symbol	Test Condition	V <sub>CC</sub> (V)	Min	Тур.	Max	Unit
High-level input voltage ( $\overline{OE}$ , SEL)	V <sub>IH</sub>	_	1.65 to 3.6	$0.65 \times V_{CC}$	—	—	V
Low-level input voltage (OE, SEL)	V <sub>IL</sub>	l	1.65 to 3.6		—	$0.35 \times V_{CC}$	V
Input leakage current (OE, SEL)	I <sub>IN</sub>	V <sub>IN</sub> = 0 to 3.6 V	1.65 to 3.6	_	—	±1	μA
Switch OFF-state leakage current	I <sub>SZ</sub>	$\frac{V_{IS}}{OE} = 0 \text{ to } 2.5 \text{ V},$ $\frac{V_{IS}}{OE} = V_{CC}$	1.65 to 3.6	_	—	±3	μA
ON-resistance	R <sub>ON</sub>	V <sub>IS</sub> = 0 V, I <sub>IS</sub> = 8 mA (TDS4A212)	3.0		—	8.4	Ω
		V <sub>IS</sub> = 0 V, I <sub>IS</sub> = 8 mA (TDS4B212)	3.0	_	—	7.9	
		V <sub>IS</sub> = 2 V, I <sub>IS</sub> = 8 mA	3.0	_	—	15	
Standby current	I <sub>STB</sub>	$\frac{V_{IN}}{OE} = V_{CC} \text{ or GND},$	3.6	—	—	10	μA
Current consumption	I <sub>ope</sub>	$\frac{V_{IN}}{OE} = V_{CC} \text{ or GND},$ $\overline{OE} = GND$	3.6	_	60	150	μA

Note : All typical values are at  $T_a = 25$  °C.

### 12.1.2. DC Characteristics (Note) (Unless otherwise specified, $T_a = -40$ to 105 °C)

Characteristics	Symbol	Test Condition	V <sub>CC</sub> (V)	Min	Тур.	Max	Unit
High-level input voltage ( $\overline{OE}$ , SEL)	V <sub>IH</sub>	—	1.65 to 3.6	$0.65 \times V_{CC}$	_	—	V
Low-level input voltage (OE, SEL)	V <sub>IL</sub>	_	1.65 to 3.6			$0.35 \times V_{CC}$	V
Input leakage current (OE, SEL)	I <sub>IN</sub>	V <sub>IN</sub> = 0 to 3.6 V	1.65 to 3.6	_		±1	μA
Switch OFF-state leakage current	I <sub>SZ</sub>	$\frac{V_{IS}}{OE} = 0 \text{ to } 2.5 \text{ V},$ $\overline{OE} = V_{CC}$	1.65 to 3.6			±4	μA
ON-resistance	R <sub>ON</sub>	V <sub>IS</sub> = 0 V, I <sub>IS</sub> = 8 mA (TDS4A212)	3.0	_	_	8.9	Ω
		V <sub>IS</sub> = 0 V, I <sub>IS</sub> = 8 mA (TDS4B212)	3.0	—	_	8.4	
		V <sub>IS</sub> = 2 V, I <sub>IS</sub> = 8 mA	3.0	_	—	16	
Standby current	I <sub>STB</sub>	$\frac{V_{IN}}{OE} = V_{CC} \text{ or GND},$ $\frac{V_{IN}}{OE} = V_{CC}$	3.6	—	_	10	μA
Current consumption	I <sub>ope</sub>	$\frac{V_{IN}}{OE} = V_{CC} \text{ or GND},$ $\overline{OE} = GND$	3.6	_	60	150	μA

Note: All typical values are at  $T_a = 25$  °C.

### 12.2. High frequency characteristics (Note) (Unless otherwise specified, $V_{CC}$ = 1.6 to 3.6 V)

### 12.2.1. TDS4A212MX

Characteristics	Symbol	Note	Test Condition		Тур.	Unit				
-3-dB Bandwidth (differential)	BW <sub>(Diff)</sub>	(Note 1)	$R_L$ = 50 $\Omega$ , See Fig. 13.1		26.2	GHz				
Differential insertion loss	DDIL	(Note 1)	R <sub>L</sub> = 50 Ω	f = 2.5 GHz	-0.7	dB				
			See Fig. 13.1	f = 4.0 GHz	-0.8					
				f = 5.0 GHz	-0.9	]				
				f = 8.0 GHz	-1.0					
				f = 10.0 GHz	-1.1					
				f = 12.8 GHz	-1.4	]				
				f = 16.0 GHz	-1.9					
Differential return loss	DDRL	(Note 1)	R <sub>L</sub> = 50 Ω	f = 2.5 GHz	-18	dB				
			See Fig. 13.1	f = 4.0 GHz	-19	]				
				f = 5.0 GHz	-15					
				f = 8.0 GHz	-14	]				
				f = 10.0 GHz	-17					
				f = 12.8 GHz	-17					
								f = 16.0 GHz	-18	
Differential OFF isolation	DDOIRR	(Note 1)	R <sub>L</sub> = 50 Ω	f = 2.5 GHz	-25	dB				
	See Fig. 13.2	See Fig. 13.2	f = 4.0 GHz	-22						
				f = 5.0 GHz	-20					
				f = 8.0 GHz	-19	]				
				f = 10.0 GHz	-17					
				f = 12.8 GHz	-12	]				
				f = 16.0 GHz	-11					
Differential Crosstalk	DDXT	(Note 1)		f = 2.5 GHz	-40	dB				
			See Fig. 13.3, 13.4	f = 4.0 GHz	-37	]				
				f = 5.0 GHz	-36					
				f = 8.0 GHz	-34	]				
				f = 10.0 GHz	-32	]				
				f = 12.8 GHz	-31					
				f = 16.0 GHz	-30	]				

Note: All typical values are at  $T_a = 25$  °C.

Note 1: Parameter guaranteed by design.

### 12.2.2. TDS4B212MX

Characteristics	Symbol	Note	Test Condition	est Condition		Unit	
-3-dB Bandwidth (differential)	BW <sub>(Diff)</sub>	(Note 1)	R <sub>L</sub> = 50 Ω, See Fig. 13.1		27.5	GHz	
Differential insertion loss	loss DDIL (Note	(Note 1)	R <sub>L</sub> = 50 Ω	f = 2.5 GHz	-0.7	dB	
			See Fig. 13.1	f = 4.0 GHz	-0.8	1	
				f = 5.0 GHz	-0.8	1	
				f = 8.0 GHz	-0.9	]	
				f = 10.0 GHz	-0.9	]	
				f = 12.8 GHz	-1.2		
				f = 16.0 GHz	-1.4		
Differential return loss	DDRL	(Note 1)		f = 2.5 GHz	-20	dB	
			See Fig. 13.1	f = 4.0 GHz	-18		
				f = 5.0 GHz	-17		
				f = 8.0 GHz	-15	]	
				f = 10.0 GHz	-20	]	
				f = 12.8 GHz	-17		
				f = 16.0 GHz	-16	]	
Differential OFF isolation	DDOIRR	(Note 1)	R <sub>L</sub> = 50 Ω	f = 2.5 GHz	-25	dB	
			See Fig. 13.2	f = 4.0 GHz	-21		
				f = 5.0 GHz	-20		
					f = 8.0 GHz	-17	]
			f = 10.0 GHz	-16	]		
				f = 12.8 GHz	-17	]	
				f = 16.0 GHz	-14		
Differential Crosstalk	DDXT	(Note 1)		f = 2.5 GHz	-68	dB	
			See Fig. 13.3, 13.4	f = 4.0 GHz	-60	]	
				f = 5.0 GHz	-56	]	
				f = 8.0 GHz	-48	]	
				f = 10.0 GHz	-44	]	
				f = 12.8 GHz	-39	]	
				f = 16.0 GHz	-36	]	

Note: All typical values are at  $T_a = 25$  °C. Note 1: Parameter guaranteed by design.

### 12.3. Switching Characteristics (Unless otherwise specified, Ta = 25 °C)

### 12.3.1. TDS4A212MX

Characteristics	Symbol	Note	Test Condition	V <sub>CC</sub> (V)	Тур.	Max	Unit
Propagation delay time	t <sub>PLH</sub> /t <sub>PHL</sub>	(Note 1)	R <sub>L</sub> = 50 Ω, f = 10 GHz See Fig. 13.1, 13.7	3.3	33	_	ps
Output skew (bit to bit)	t <sub>SK(b)</sub>	(Note 1)	R <sub>L</sub> = 50 Ω, f = 10 GHz See Fig. 13.1, 13.8	3.3	6	_	ps
Output skew (channel to channel)	t <sub>SK(CH)</sub>	(Note 1)	R <sub>L</sub> = 50 Ω, f = 10 GHz See Fig. 13.1, 13.7	3.3	6	—	ps

Note 1: Parameter guaranteed by design.

### 12.3.2. TDS4B212MX

Characteristics	Symbol	Note	Test Condition	V <sub>CC</sub> (V)	Тур.	Max	Unit
Propagation delay time	t <sub>PLH</sub> /t <sub>PHL</sub>	(Note 1)	R <sub>L</sub> = 50 Ω, f = 10 GHz See Fig. 13.1, 13.7	3.3	30	—	ps
Output skew (bit to bit)	t <sub>SK(b)</sub>	(Note 1)	R <sub>L</sub> = 50 Ω, f = 10 GHz See Fig. 13.1, 13.8	3.3	4	—	ps
Output skew (channel to channel)	t <sub>SK(CH)</sub>	(Note 1)	R <sub>L</sub> = 50 Ω, f = 10 GHz See Fig. 13.1, 13.7	3.3	2	_	ps

Note 1: Parameter guaranteed by design.

### 12.4. Timing characteristics

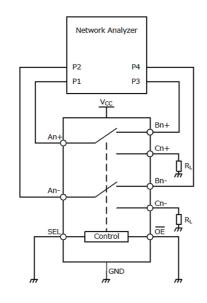
### 12.4.1. Timing characteristics (Unless otherwise specified, $T_a = -45$ to 85 °C)

Characteristics	Symbol	Test Condition	V <sub>CC</sub> (V)	Min	Тур.	Max	Unit
Start-up time.	t <sub>sup</sub>	See Fig. 13.5	1.65 to 3.6	_	—	100	μS
Turn-ON time (SEL to Output)	t <sub>on</sub>	$R_L = 50 \Omega$ , $C_L = 5 pF$ See Fig. 13.5	1.65 to 3.6	_	—	180	ns
Turn-ON time ( $\overline{OE}$ to Output)			1.65 to 3.6		_	100	μS
Turn-OFF time (SEL to Output)	t <sub>off</sub>	$R_L = 50 \Omega$ , $C_L = 5 pF$ See Fig. 13.5	1.65 to 3.6	_	_	18	ns
Turn-OFF time ( $\overline{OE}$ to Output)			1.65 to 3.6	_	—	21	
Break before make	TBBM	R <sub>L</sub> = 50 Ω, C <sub>L</sub> = 5 pF See Fig. 13.6	1.65 to 3.6	55	—	160	ns

### 12.4.2. Timing characteristics (Unless otherwise specified, $T_a = -45$ to 105 °C)

Characteristics	Symbol	Test Condition	V <sub>CC</sub> (V)	Min	Тур.	Max	Unit
Start-up time.	t <sub>sup</sub>	See Fig. 13.5	1.65 to 3.6	_	_	110	μS
Turn-ON time (SEL to Output)	t <sub>on</sub>	$R_L$ = 50 Ω, $C_L$ = 5 pF See Fig. 13.5	1.65 to 3.6	_	_	180	ns
Turn-ON time (OE to Output)			1.65 to 3.6	_	_	110	μS
Turn-OFF time (SEL to Output)	t <sub>off</sub>	$R_L$ = 50 Ω, $C_L$ = 5 pF See Fig. 13.5	1.65 to 3.6	_	—	20	ns
Turn-OFF time ( $\overline{OE}$ to Output)			1.65 to 3.6	_	_	25	
Break before make	TBBM	$R_L = 50 \Omega$ , $C_L = 5 pF$ See Fig. 13.6	1.65 to 3.6	55	—	160	ns

### 13. AC Electrical Test Circuit (Fig)

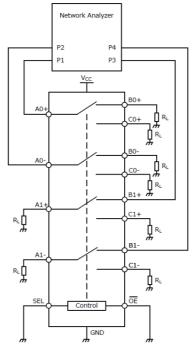


R<sub>L</sub> = 50 Ω

All unused ports are connected to GND through 50  $\Omega$  pull-down resistors. This figure is an example showing how to measure An and Bn.

Fig. 13.1 -3-dB Bandwidth(differential), Differential insertion loss,Differential return loss, Propagation delay time,

Output skew (channel to channel, bit to bit)

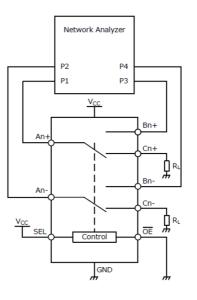


 $R_L = 50 \ \Omega$ 

All unused ports are connected to GND through 50  $\Omega$  pull-down resistors.

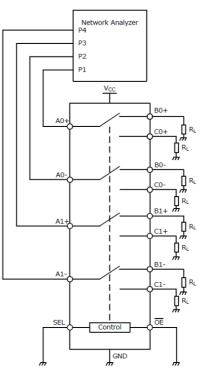
This figure is an example showing how to measure A0 and B1.

Fig. 13.3 Differential Far-end crosstalk



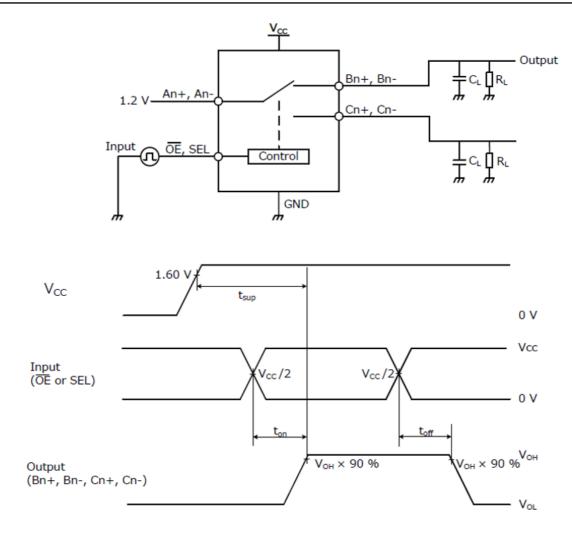
 $\rm R_L$  = 50  $\Omega$  All unused ports are connected to GND through 50  $\Omega$  pull-down resistors. This figure is an example showing how to measure An and Bn.

#### Fig. 13.2 Differential OFF isolation



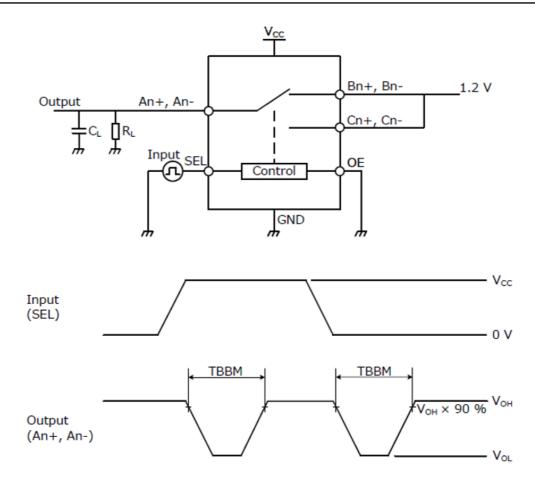
 $R_L=50~\Omega$  All unused ports are connected to GND through  $50~\Omega$  pull-down resistors. This figure is an example showing how to measure A0 and A1.

#### Fig. 13.4 Differential Near-end crosstalk

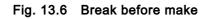


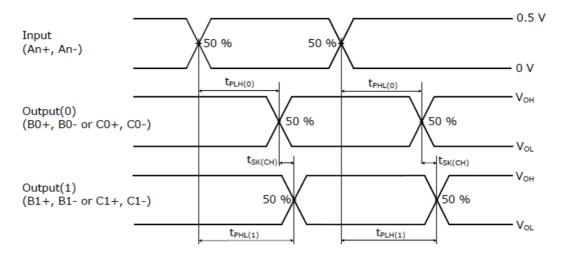
$$R_L = 50 \Omega, C_L = 5 pF$$

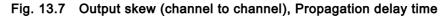
Fig. 13.5 Start-up, Turn-ON and Turn-OFF time



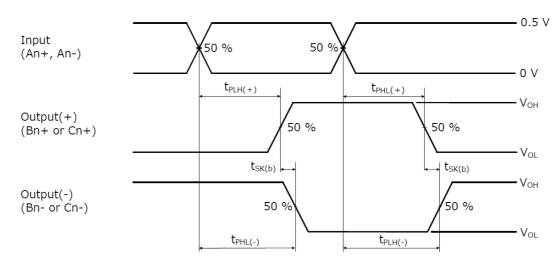
 $R_L = 50 \Omega, C_L = 5 pF$ 

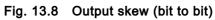






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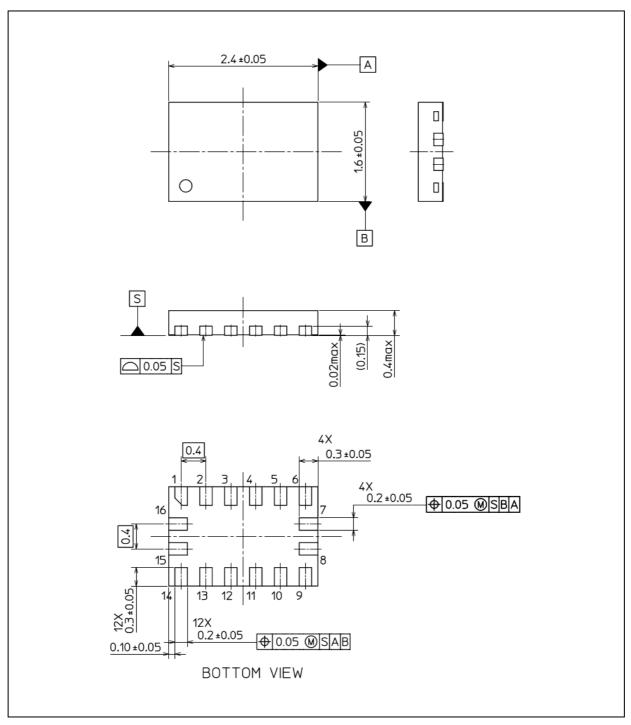




### TDS4A212MX,TDS4B212MX

### **Package Dimensions**

Unit: mm



Weight: 3.9 mg (typ.)

Package Name(s)

Nickname: XQFN16

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